

a source region having the second conductive type semiconductor provided on  
 the channel region, the source region is located substantially at a center of the channel region,  
 and the source region is isolated from the insulation film; and  
*Sub*  
 a source electrode connected to the source region,  
 wherein a depletion layer is formed over most of the entire channel region  
 when a predetermined voltage is applied to the gate region.

4. (Three Times Amended) The semiconductor device according to claim 1,  
 [21] of Fig. 5  
 further comprising a semiconductor region having the first conductive type semiconductor  
 and provided between the channel region and the source electrode.

REMARKS

Claims 1, 4, 12 and 20-30 are pending. By the preliminary Amendment, claims 1 and  
 4 are amended adding the term "semiconductor". Prompt and favorable examination on the  
 merits is respectfully solicited.

Respectfully submitted,

  
 James A. Oliff  
 Registration No. 27,075

Richard J. Kim  
 Registration No. 48,360

JAO:RJK/sld

Attachments:

Appendix  
 Petition for Extension of Time

Date: May 17, 2002

**OLIFF & BERRIDGE, PLC**  
 P.O. Box 19928  
 Alexandria, Virginia 22320  
 Telephone: (703) 836-6400

<b>DEPOSIT ACCOUNT USE AUTHORIZATION</b> Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
--

## APPENDIX

1. (Three-Four Times Amended) A bipolar semiconductor device comprising:
  - a drain electrode;
  - a drain region having a first conductive type semiconductor and disposed on the drain electrode;
  - a drift region having a second conductive type semiconductor different from the first conductive type semiconductor of the drain region and disposed on the drain region;
  - a channel region having the second conductive type semiconductor and disposed on the drift region;
  - a gate region surrounding at least a part of the channel region via an insulation film, the gate region having the first conductive type semiconductor;
  - a source region having the second conductive type semiconductor provided on the channel region, the source region is located substantially at a center of the channel region, and the source region is isolated from the insulation film; and
  - a source electrode connected to the source region,  
wherein a depletion layer is formed over most of the entire channel region when a predetermined voltage is applied to the gate region.

4. (Twice-Three Times Amended) The semiconductor device according to claim 1, further comprising a semiconductor region having the first conductive type semiconductor and provided between the channel region and the source electrode.